600V, 15A, Trench FS II Fast IGBT

General Description:

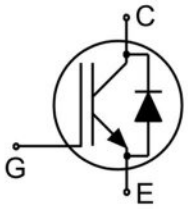
Using MJ's proprietary trench design and advanced FS (Field Stop) second generation technology, the 600V Trench FSII IGBT offers superior conduction and switching performances, and easy parallel operation;

Features

- ◆ Trench FSII Technology offering
- ◆ Very low $V_{CE\ (sat)}$
- ◆ High speed switching
- ◆ Positive temperature coefficient in $V_{CE\ (sat)}$
- ◆ Very tight parameter distribution
- ◆ High ruggedness, temperature stable behavior

Application

- ◆ Air Condition
- ◆ Inverters
- ◆ Motor drives



Schematic diagram

TO-220

Package Marking and Ordering Information

Device	Device Package	Device Marking
MJ15TD60	TO-220	MJ15TD60

Absolute Maximum Ratings (T_C=25°C unless otherwise noted)

Parameter	Symbol	Value	Units
Collector-Emitter Voltage	V_{CES}	600	V
Gate- Emitter Voltage	V_{GES}	±30	V
Collector Current	I_C	30	A
Collector Current @T_C = 100 °C	I_C	15	A
Pulsed Collector Current, t_p limited by T_{jmax}	I_{Cplus}	45	A
turn off safe operating area, V_{CE}=600V, Tj=150°C	-	45	A
Diode Continuous Forward Current @T_C = 100 °C	I_F	15	A
Diode Maximum Forward Current	I_{FM}	45	A
Power Dissipation @ T_C = 25°C	P_D	105	W
Power Dissipation @T_C = 100 °C	P_D	42	W
Operating Junction and Storage Temperature Range	T_J,T_{stg}	-55 to +150	℃
Maximum Temperature for Soldering	T_L	260	℃
Short circuit withstand time V_{GE}=15.0V, V_{CC}≤400V, Allowed number of short circuits<1000Time between short circuits:≥1.0s,Tj≤150°C	t_{sc}	10	us

Thermal Characteristic

Parameter	Symbol	Value	Units
Thermal Resistance, Junction to case for IGBT	$R_{\theta JC}$	1.19	°C/W
Thermal Resistance, Junction to case for Diode	$R_{\theta JC}$	1.92	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	62	°C/W

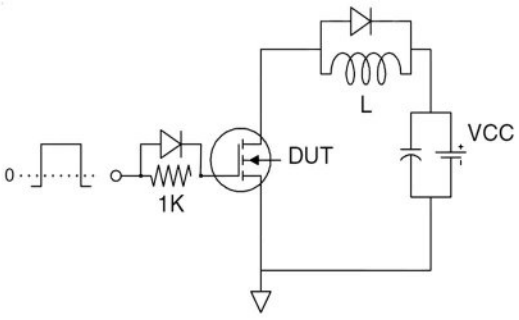
Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Value			Units
			Min	Typ	Max	
Static Characteristics						
Collector-Emitter Breakdown Voltage	$V_{(BR)CES}$	V_{GE}=0V,I_{CE}=1mA	600	-	-	V
Collector-Emitter Leakage Current	I_{CES}	V_{GE}=0V,V_{CE}=600V	-	-	4	uA
Gate to Emitter Forward Leakage	$I_{GES(F)}$	V_{GE}=+30V,V_{CE}=0V	-	-	100	nA
Gate to Source Reverse Leakage	$I_{GES(R)}$	V_{GE}=-30V,V_{CE}=0V	-	-	100	nA
ON Characteristics						
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=15A,V_{GE}=15V	-	1.8	2.0	V
Gate Threshold Voltage	$V_{GE(th)}$	I_C=1mA,V_{CE}=V_{GE}	4.0	5.0	6.0	V
Dynamic Characteristics						
Input Capacitance	C_{ies}	V_{CE}=25V,V_{GE}=0V, f=1MHz	-	649	-	pF
Output Capacitance	C_{oss}		-	61	-	pF
Reverse Transfer Capacitance	C_{rss}		-	27	-	pF
Gate Charge	Q_{Gate}	V_{CC}=480V, I_C=15A V_{GE}=15V	-	75	-	nC
Short circuit collector current Max.1000 short circuits Time between short circuits: ≥1.0s	$I_{C(SC)}$	V_{GE}=15V,V_{CC}≤400V, t_{SC}≤10us,T_j≤150°C	-	70	-	A
Switching Characteristics						
Turn-on Delay Time	$t_{d(ON)}$	V_{CC}=400V,I_C=15A V_{GE}=0/15V, R_g=15Ω Inductive Load	-	17	-	ns
Rise Time	t_r		-	18	-	ns
Turn-Off Delay Time	$t_{d(OFF)}$		-	114	-	ns
Fall Time	t_f		-	41	-	ns
Turn-On Switching Loss	E_{on}		-	0.60	-	mJ
Turn-Off Switching Loss	E_{off}		-	0.38	-	mJ
Total Switching Loss	E_{ts}		-	0.98	-	mJ

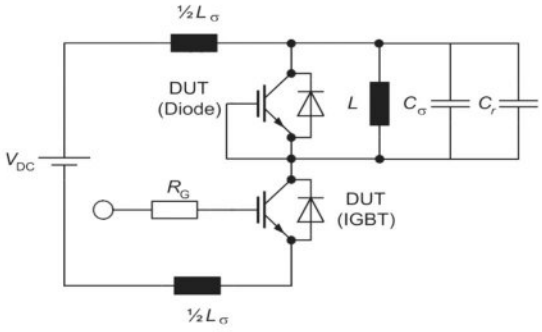
Electrical Characteristics of the Diode (T_C= 25°C unless otherwise specified):

Parameter	Symbol	Test Conditions	Rating			Units
			Min	Typ	Max	
Diode Forward Voltage	V_{FM}	I_F=15A	-	1.45	1.7	V
Reverse Recovery Time	T_{rr}	V_{cc}=400V, I_F=15A, di/dt=800A/uS	-	122	-	ns
Diode Peak Reverse Recovery Current	I_{RRM}		-	13	-	A
Reverse Recovery Charge	Q_{rr}		-	1.04	-	uC
Pulse width ttp≤380μs,δ≤2%						

Test Circuit

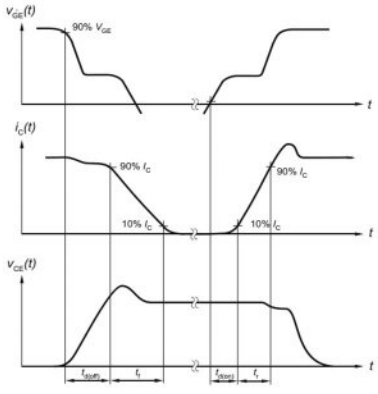


Gate Charge Test Circuit

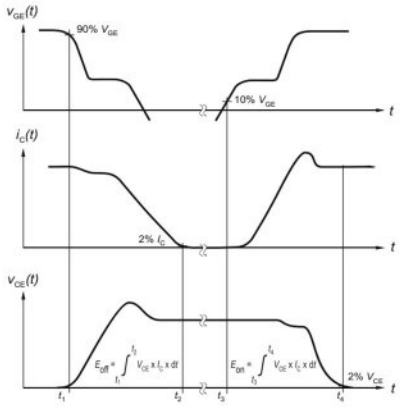


Switch Time Test Circuit

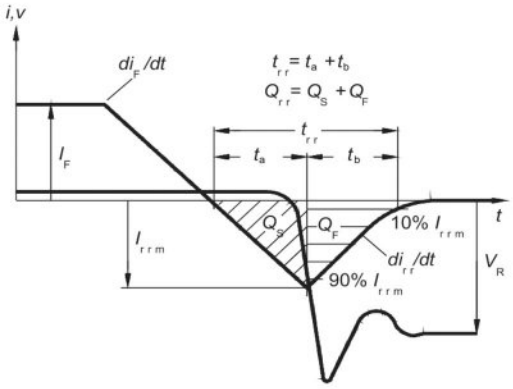
Switching characteristics



definition of switching times



definition of switching losses



Definition of diode switching characteristics

Typical Electrical and Thermal Characteristics

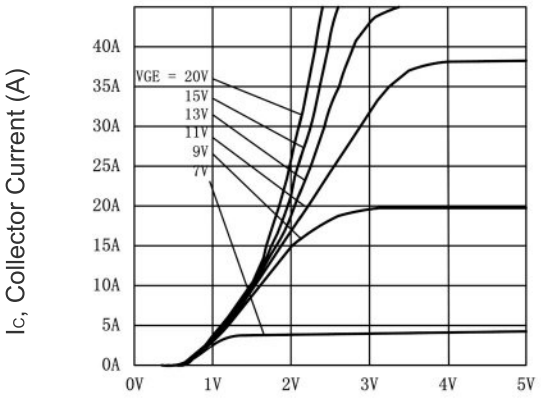


Figure 1 Output Characteristics

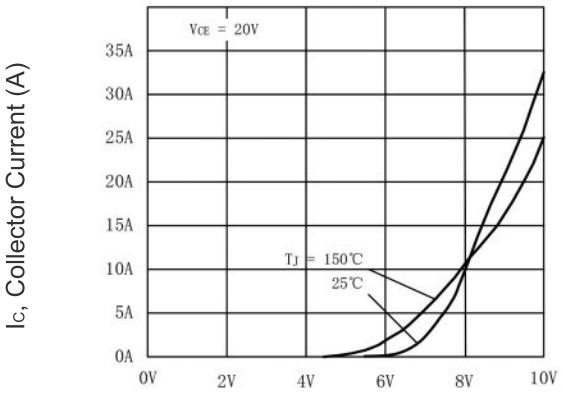


Figure 2 Transfer Characteristics

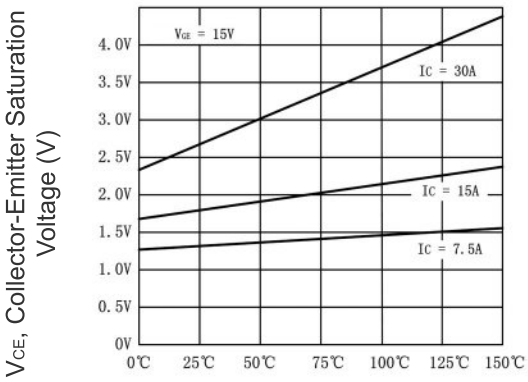


Figure 3 V_{CEsat} vs. Case Temperature

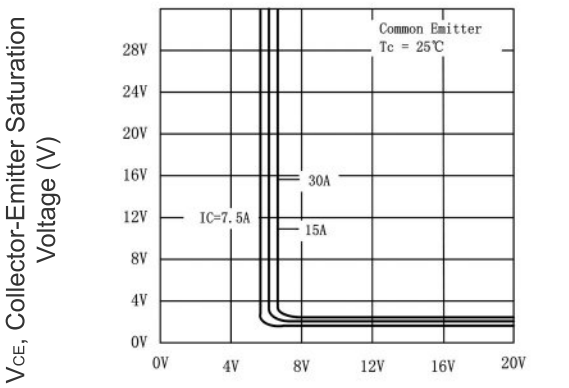


Figure 4 Saturation Voltage vs. V_{GE}

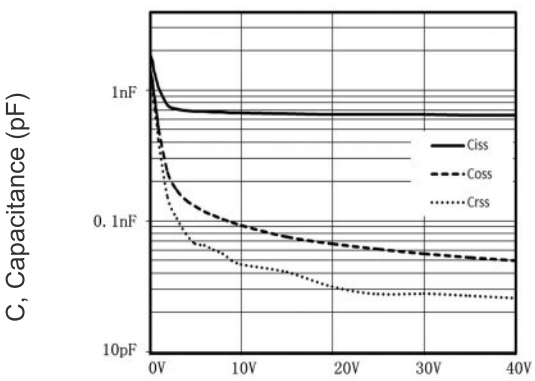


Figure 5 Capacitance Characteristics

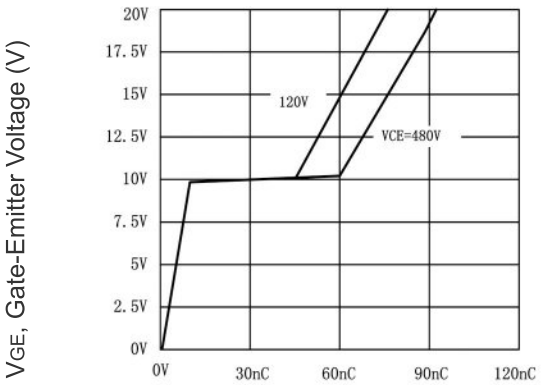


Figure 6 Gate charge waveform

Typical Electrical and Thermal Characteristics（continued）

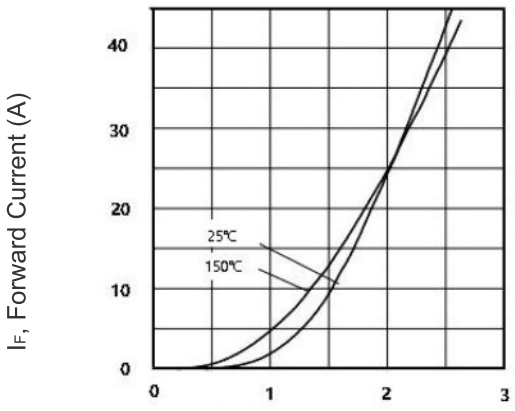


Figure 7 Forward Characteristics

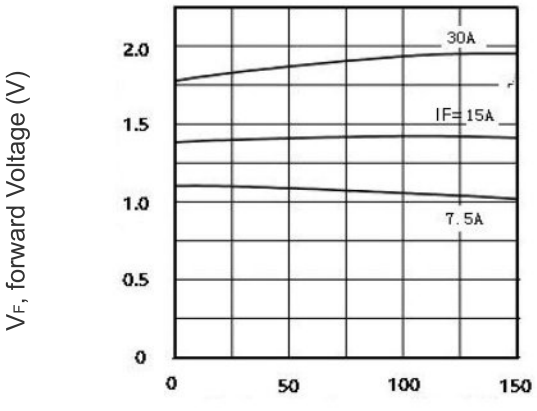


Figure 8 V_F vs. temperature

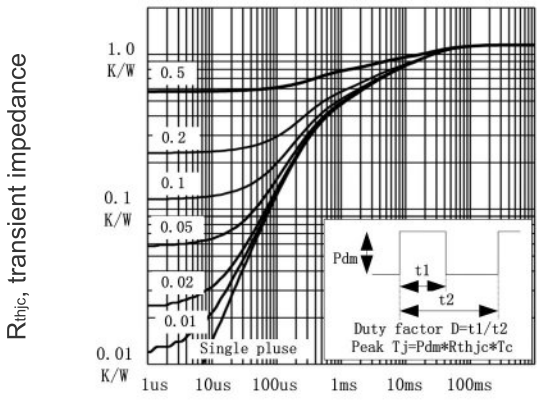
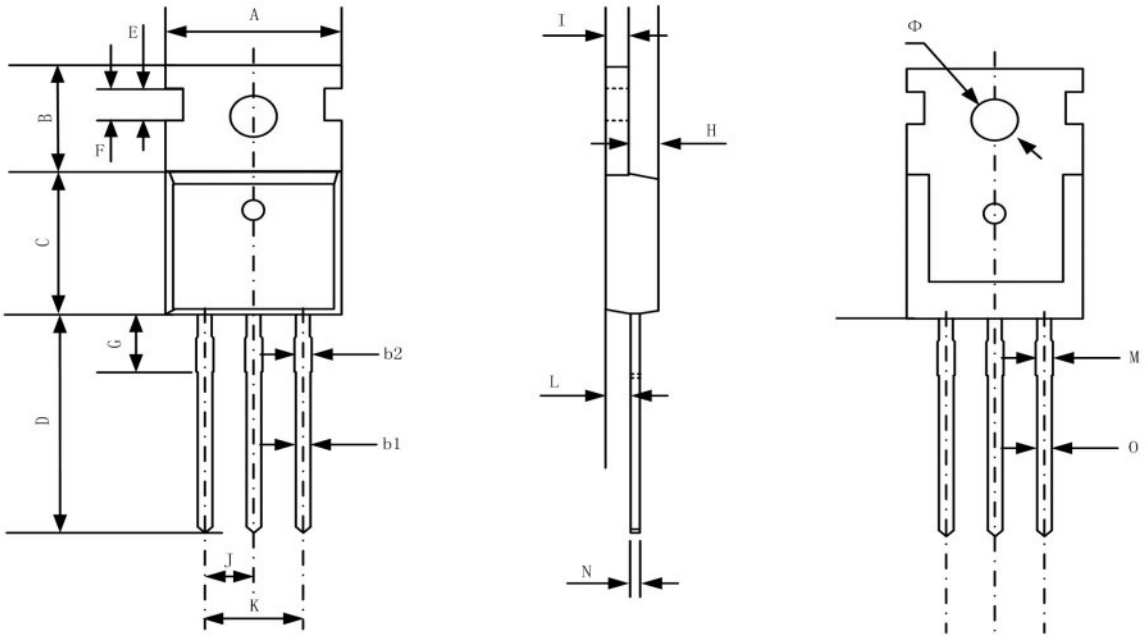


Figure 9 Transient Thermal Impedance of IGBT

TO-220-3L-C Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	9.70	10.10	0.38	0.40
B	6.30	6.70	0.25	0.26
C	9.00	9.47	0.35	0.37
D	12.80	13.30	0.50	0.52
E	1.20	1.40	0.05	0.06
F	1.70 REF		0.067 REF	
G	2.65 REF		0.104 REF	
H	3.00	3.40	0.12	0.13
I	1.25	1.40	0.05	0.06
J	2.40	2.70	0.09	0.11
K	5.00	5.15	0.20	0.20
L	2.20	2.60	0.09	0.10
M	1.25	1.45	0.05	0.06
N	0.45	0.60	0.02	0.02
O	0.70	0.90	0.03	0.04
Φ	3.6 REF		0.142 REF	

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